of a specific surface area of 50 m^2/g dispersed in water of pH 6 to 8.

5. (amended) The CMP abrasive according to Claim 1, wherein said organic polymer is a compound having an adsorption ratio of 40% or more with respect to silicon nitride particles of a specific surface area of 3.3 m^2/g dispersed in water of pH 6 to 8.

A1

6. (amended) The CMP abrasive according to Claim 1, wherein the sedimentation speed of cerium oxide particles is 20 μm/s or less.

7. (amended) The CMP abrasive according to Claim 1, wherein said organic polymer is polyvinyl pyrrolidone.

10. (amended) A method for polishing a substrate comprising polishing by moving a substrate on which a film to be polished is formed and a polishing platen while pressing the substrate against the polishing platen and a polishing cloth and supplying said CMP abrasive according to Claim 1, between the film to be polished and the polishing cloth.

A2

11. (amended) A method for manufacturing a semiconductor device comprising a step of polishing a film to be polished by moving a substrate on which the film to be polished is formed and a polishing platen while pressing the substrate against the polishing platen and a polishing cloth and supplying said CMP abrasive according to Claim 1, between the film to be polished and the polishing cloth.